

1. General description

Planar passivated high commutation three quadrant triac in a SOT428 (DPAK) surface mountable plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series B" triac will commutate the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- High voltage capability
- Less sensitive gate for very high noise immunity
- · Planar passivated for voltage ruggedness and reliability
- Surface mountable package
- Triggering in three quadrants only

3. Applications

- Electronic thermostats
- General purpose motor controls
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 102 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	-	8	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	-	65	A
		full sine wave; $T_{j(init)} = 25 \text{ °C};$ t _p = 16.7 ms	-	-	72	A
Тj	junction temperature		-	-	125	°C
Static chara	acteristics	·				
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	2	18	50	mA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	2	21	50	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	2	34	50	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	31	60	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
Dynamic cha	racteristics	·				
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	1000	4000	-	V/µs
dl _{com} /dt	rate of change of commutating current	$ V_D = 400 \text{ V}; \text{T}_{\text{j}} = 125 ^\circ\text{C}; \text{I}_{\text{T}(\text{RMS})} = 8 \text{ A}; \\ $	-	14	-	A/ms

5. Pinning information

Table 2. F	Pinning inf	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	[]	T2T1
2	T2	main terminal 2		sym051
3	G	gate		Symost
mb	Τ2	mounting base; main terminal 2	DPAK (SOT428)	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BTA208S-600B	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428				

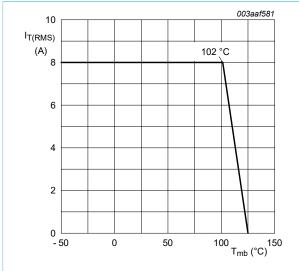


7. Limiting values

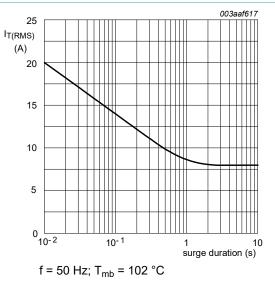
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 102 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	8	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	65	A
		full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms	-	72	А
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	21	A²s
dl _T /dt	rate of rise of on-state current	I _G = 100 mA	-	100	A/µs
I _{GM}	peak gate current		-	2	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

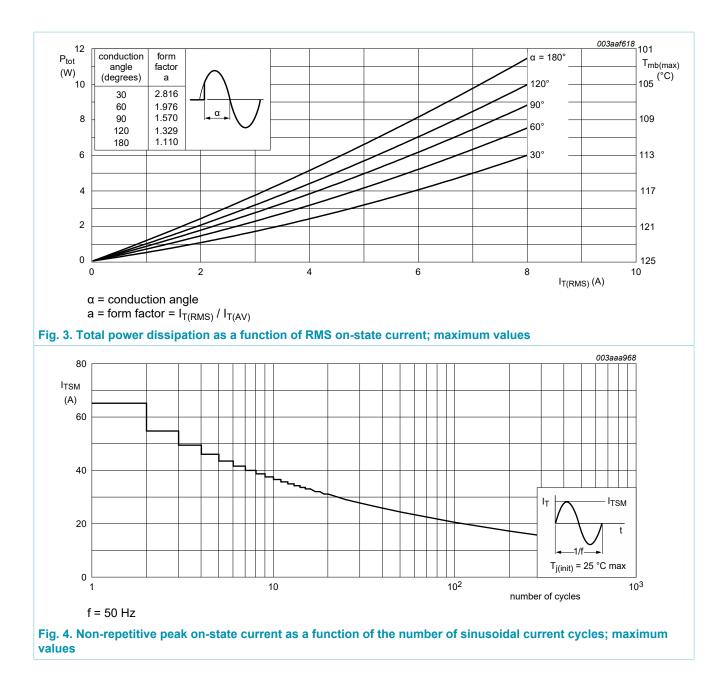






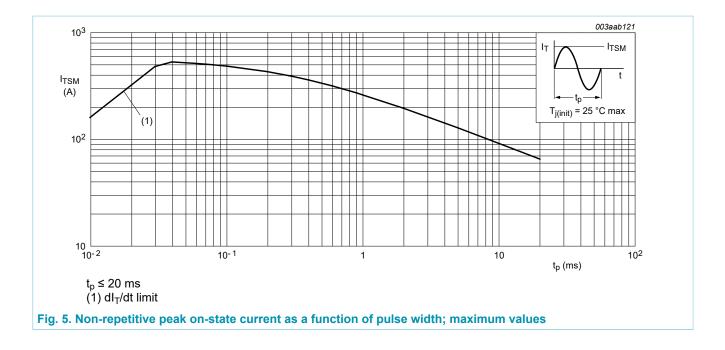


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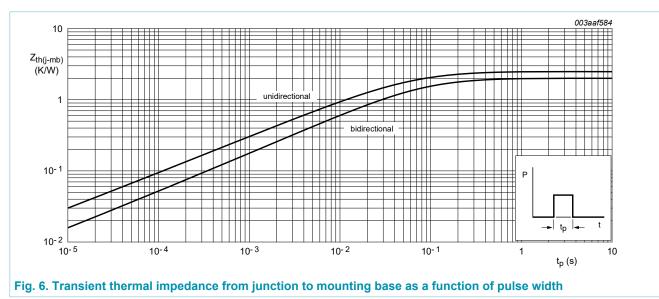




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8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	full cycle; <u>Fig. 6</u>	-	-	2	K/W
	from junction to mounting base	half cycle; <u>Fig. 6</u>	-	-	2.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted	-	75	-	K/W



BTA208S-600B

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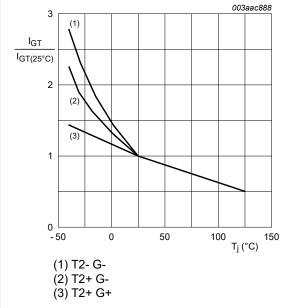
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9. Characteristics

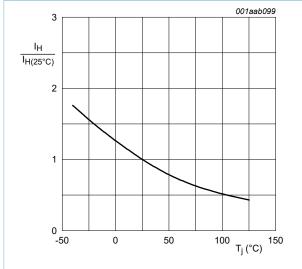
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		· · ·			
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	2	18	50	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	2	21	50	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	2	34	50	mA
۱L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	31	60	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 8</u>	-	34	90	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 8</u>	-	30	60	mA
Iн	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	31	60	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; <u>Fig. 11</u>	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	1000	4000	-	V/µs
dl _{com} /dt	rate of change of commutating current	$ V_D = 400 \text{ V}; \text{T}_\text{j} = 125 ^\circ\text{C}; \text{I}_\text{T(RMS)} = 8 \text{ A}; \\ d\text{V}_\text{com}/\text{dt} = 20 \text{V}/\mu\text{s}; \text{ snubberless} \\ condition; \text{ gate open circuit; } \underline{\text{Fig. 12}} $	-	14	-	A/ms
t _{gt}	gate-controlled turn-on time	I_{TM} = 12 A; V _D = 600 V; I _G = 0.1 A; dI _G / dt = 5 A/µs	-	2	-	μs

BTA208S-600B

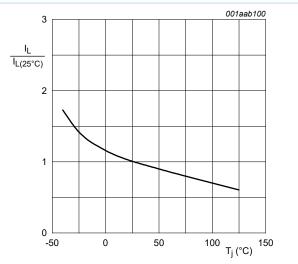
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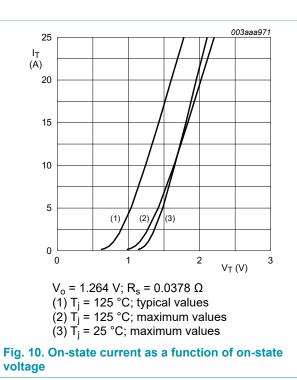






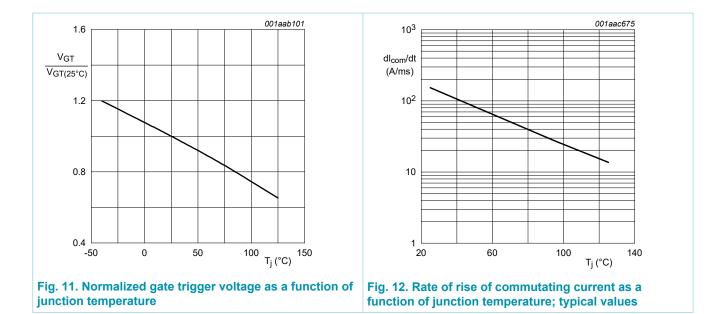






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10. Package outline

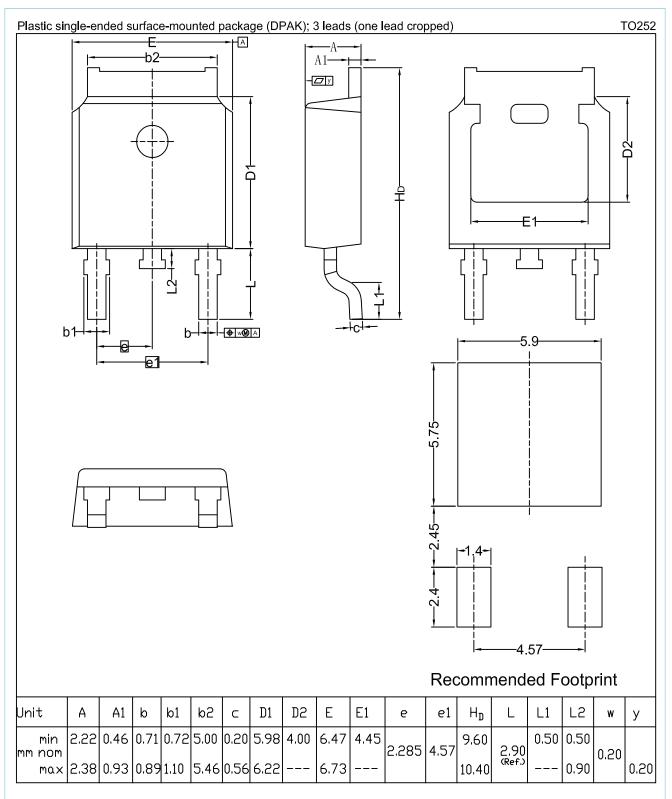


Fig. 13. Package outline DPAK (SOT428)

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Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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- [2] The term 'short data sheet' is explained in section "Definitions".
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12. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Limiting values	3
8.	Thermal characteristics	6
9.	Characteristics	7
10.	. Package outline	10
11.	. Legal information	11

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